



P-CHANNEL ENHANCEMENT MODE MOSFET

Features

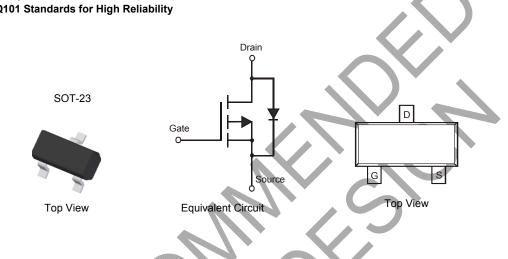
Low On-Resistance:

 $R_{DS(ON)} < 120 m\Omega @ V_{GS} = -4.5V$ $R_{DS(ON)} < 240 m\Omega @ V_{GS} = -2.5V$

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

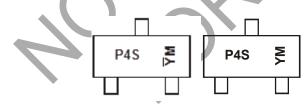


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3120L-7	SOT-23	3000/Tape & Reel

- Notes:
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



P4S = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013)

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Chengdu A	v
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9 =September)

ngdu	A/T	Site	

Chengdu

Shanghai	A/T	Site

	W = Wonth	(ex: 9 = Sep
Site		

Date Code Key												
Year	2008	;	2009	2010)	2011	2012	2	2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V _{DSS}	-30	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 5)	T _A =+25°C T _A = +70°C	Ι _D	-2.8 -2.2	A
Drain Current (Note 5)	Pulsed	IDM	-9	А
Body-Diode Continuous Current (Note 5)		Is	-2.0	A

Thermal Characteristics

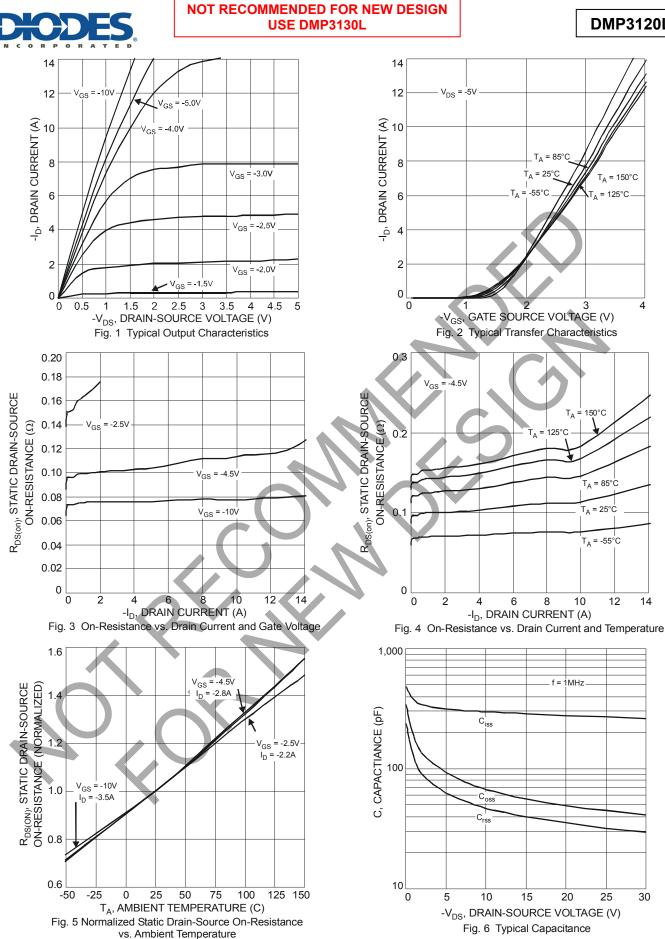
Symbol	Value	Unit
PD	1.4	W
$R_{ heta JA}$	90	°C/W
T _{J,} T _{STG}	-55 to +150	°C
	P _D R _{0JA}	P _D 1.4 R ₀ JA 90

Notes: 5. Device mounted on FR-4 PCB. t ≤5 sec.

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)	• • • • • •		76			
Drain-Source Breakdown Voltage	BV _{DSS}	-30			V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	+		-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS} 🗼			±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.6		-1.4	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	R _{DS (ON)}	+		120 240	mΩ	V _{GS} = -4.5V, I _D = -2.8A V _{GS} = -2.5V, I _D = -1.8A
Forward Transconductance	g fs	_	5		S	V _{DS} = -5V, I _D = -2.8A
Source-Drain Diode Forward Voltage	V _{SD}		-	-1.1	V	V _{GS} = 0V, I _S = -2.0A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss		285		pF	
Output Capacitance	Coss		56	_	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		40	_	pF	
Gate Resistance	R _G		13	_	Ω	V _{DS} = 0V, V _{GS} = 0V f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 7)						
Turn-On Delay Time	t _{d(on)}	_	5.6			
Rise Time	tr	_	6.8		ns	V _{DS} = -15V, V _{GS} = -4.5V,
Turn-Off Delay Time	t _{d(off)}	_	35.3	_	115	$I_{\rm D}$ = -1A, $R_{\rm G}$ = 6.0 Ω
Fall Time	tf	_	19.2	_		
Total Gate Charge	Q_{G}	_	6.7 3.0	_	20	V _{DS} = -15V, V _{GS} = -10V, I _D = -1.0A
Gate-Source Charge	Q _{GS}		0.8	—	nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -1.0A
Gate-Drain Charge	Q_{GD}		0.5			

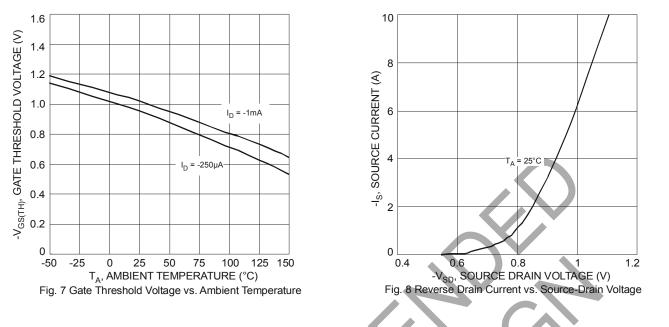
Notes:6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to production testing.



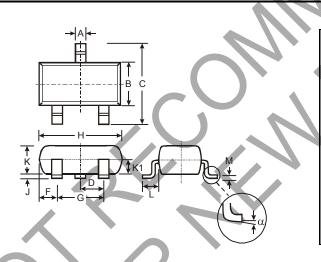


NOT RECOMMENDED FOR NEW DESIGN USE DMP3130L

DMP3120L

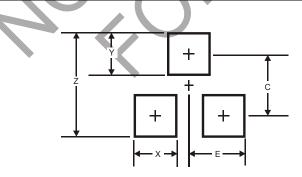


Package Outline Dimensions



SOT-23				
Dim	Min	Max	Тур	
Α	0.37	0.51	0.40	
В	1.20	1.40	1.30	
С	2.30	2.50	2.40	
D	0.89	1.03	0.915	
F	0.45	0.60	0.535	
G	1.78	2.05	1.83	
н	2.80	3.00	2.90	
J	0.013	0.10	0.05	
κ	0.903	1.10	1.00	
K1	-	-	0.400	
L	0.45	0.61	0.55	
М	0.085	0.18	0.11	
α	0°	8°	-	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)	
Z	2.9	
Х	0.8	
Y	0.9	
С	2.0	
E	1.35	



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